

## Charge-carrier density in Semiconductors

- Density of states

- Number of available states per unit energy interval per unit volume.

$$D(E) \propto \sqrt{(E-E_c)}$$

$$D(E) = K \sqrt{(E-E_c)} \quad \text{eV}^{-1} \text{cm}^{-3}$$

↑  
constant

$$D(E=E_c) = 0$$

- What is the probability of energy-state of energy  $E$  at temperature  $T$  is filled with the electrons (holes) ?

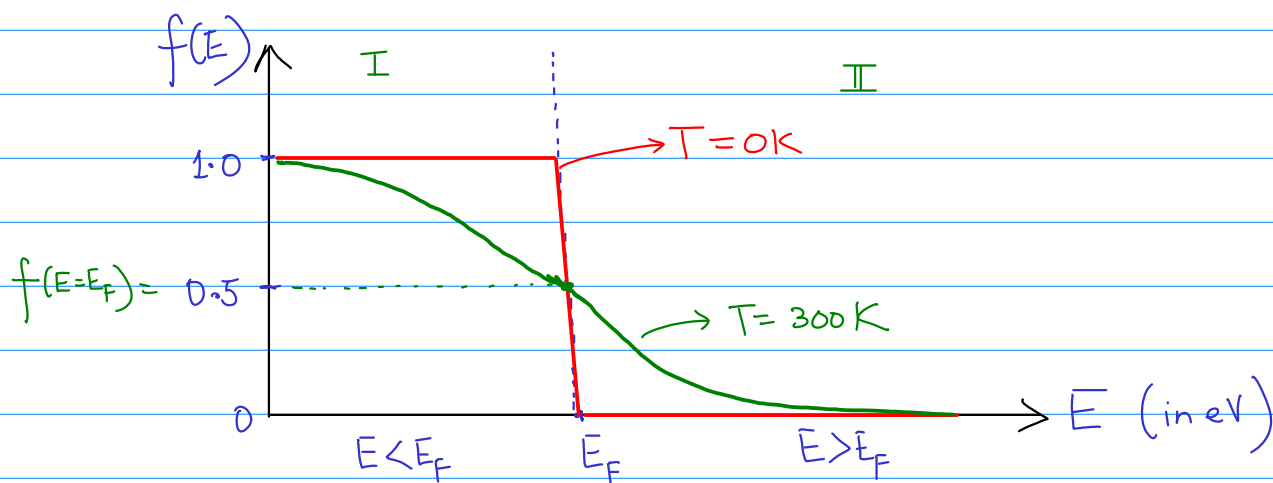
⇒ The electrons (holes) are categorized as "FERMIONS" and they follow Fermi-Dirac statistics.

$$f(E) = \frac{1}{1 + \exp\left(\frac{E-E_F}{k_B T}\right)}$$

here,  $E_F$  is termed as "FERMI-ENERGY"

$f(E)$  = Probability that an available energy state at energy  $E$  and at Temp  $T$  is occupied with the electron.

$$f(E) = \frac{1}{1 + \exp\left[\frac{E - E_F}{k_B T}\right]}$$



i) at  $T \rightarrow 0K$

a)  $E < E_F$

$$\exp\left[\frac{-(E_F - E)}{k_B T}\right] \rightarrow 0$$

$$f(E) \rightarrow 1$$

b)  $E > E_F$

$$\exp\left(\frac{E - E_F}{k_B T}\right) \rightarrow \infty$$

$$f(E) \rightarrow 0$$

ii) at  $T = 300K$

a)  $E < E_F$

$$\exp\left(\frac{-(E_F - E)}{k_B T}\right)$$

Vary  $E$  from 0 to  $E_F$

b)  $E = E_F$

$$f(E = E_F) = \frac{1}{1 + 2} = \frac{1}{3}$$

c)  $E > E_F$

$$\exp\left(\frac{E - E_F}{k_B T}\right)$$

- Now, we know the DOS in CB and how the electrons occupy the available energy-states.

Therefore, we can calculate the electron density in the conduction band at temp 'T' as

$$n = \int_{E_c}^{\infty} \underbrace{f(E)}_{\text{Probability of occupancy}} \cdot \underbrace{D(E)}_{\text{Number of electrons in CB in cm}^{-3}} dE$$

$$n = \int_{E_c}^{\infty} \frac{1}{1 + \exp\left(\frac{E - E_F}{k_B T}\right)} \cdot K \sqrt{E - E_c} \cdot dE$$

"FERMI- INTEGRAL"

Approximate Sol<sup>n</sup>:

$$n = N_c e^{-(E_c - E_F)/k_B T} \quad (\text{in cm}^{-3})$$

where,  $N_c$  = effective density of energy states

$$N_c = 2 \left( \frac{2\pi m_e^* k_B T}{h^2} \right)^{3/2} \sim 10^{19} \text{ cm}^{-3}$$

# Density of charge-carriers in Intrinsic & Extrinsic Semiconductors

